

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China







Silicon Controlled Rectifiers

Reverse Blocking Thyristors

Designed primarily for half-wave ac control applications, such as motor controls, heating controls, and power supplies; or wherever half-wave, silicon gate-controlled devices are needed.

Features

- Blocking Voltage of 600 thru 800 Volts
- On-State Current Rating of 8 Amperes RMS at 80°C
- High Surge Current Capability 80 Amperes
- Rugged, Economical TO-220AB Package
- Glass Passivated Junctions for Reliability and Uniformity
- Minimum and Maximum Values of IGT, VGT and IH Specified for Ease of Design
- High Immunity to dv/dt 100 V/μsec Minimum at 125°C
- These are Pb-Free Devices

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

| Rating | Symbol | Value | Unit |
|---|---------------------------------------|------------|--------------------|
| Peak Repetitive Off–State Voltage (Note 1) (T _J = -40 to 125°C, Sine Wave, 50 to 60 Hz, Gate Open) MCR8MG MCR8NG | V _{DRM,} V _{RRM} | 600 800 | V |
| On-State RMS Current (180° Conduction Angles; T _C = 80°C) | I _{T(RMS)} | 8.0 | Α |
| Peak Non-Repetitive Surge Current (One Full Cycle, 60 Hz, T _C = 125°C) | I _{TSM} | 80 | Α |
| Circuit Fusing Consideration (t = 8.33 ms) | I ² t | 26.5 | A ² sec |
| Forward Peak Gate Power (Pulse Width $\leq 1.0 \ \mu s, \ T_C = 80^{\circ}C)$ | P _{GM} | 5.0 | W |
| Forward Average Gate Power (t = 8.3 ms, T _C = 80°C) | P _{G(AV)} | 0.5 | W |
| Forward Peak Gate Current (Pulse Width \leq 1.0 μ s, T _C = 80°C) | I _{GM} | 2.0 | Α |
| Operating Junction Temperature Range | T _J | -40 to 125 | °C |
| Storage Temperature Range | T _{stg} | -40 to 150 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

 V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

1

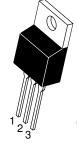


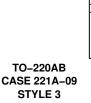
Littelfuse.com

SCRs 8 AMPERES RMS 600 thru 800 VOLTS



MARKING DIAGRAM







A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package
AKA = Diode Polarity

| PIN ASSIGNMENT | | | | |
|----------------|---------|--|--|--|
| 1 | Cathode | | | |
| 2 | Anode | | | |
| 3 | Gate | | | |
| 4 | Anode | | | |

ORDERING INFORMATION

| Device | Package | Shipping |
|--------|-----------------------|-----------------|
| MCR8NG | TO-220AB (Pb-Free) | 50 Units / Rail |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Value | Unit |
|---|-------------------------------|-------------|------|
| Thermal Resistance Junction-to-Case Junction-to-Ambient | $R_{	heta JC} \ R_{	heta JA}$ | 2.2 62.5 | °C/W |
| Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds | | 260 | °C |

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

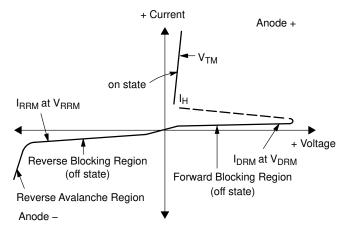
| Characteristic | | Symbol | Min | Тур | Max | Unit |
|--|---|--|--------|--------|-------------|------|
| OFF CHARACTERISTICS | | | | | | |
| Peak Repetitive Forward or Reverse Blocking Current $(V_D = Rated \ V_{DRM} \ and \ V_{RRM}; \ Gate \ Open)$ | T _J = 25°C T _J = 125°C | I _{DRM} , I _{RRM} | _ _ | _ _ | 0.01 2.0 | mA |
| ON CHARACTERISTICS | | | | | | |
| Peak Forward On-State Voltage (Note) (I _{TM} = 16 A) | | V _{TM} | - | _ | 1.8 | V |
| Gate Trigger Current (Continuous dc) $(V_D = 12 \ V; \ R_L = 100 \ \Omega)$ | | I _{GT} | 2.0 | 7.0 | 15 | mA |
| Holding Current (V _D = 12 V, Gate Open, Initiating Current = 200 mA) | | I _H | 4.0 | 17 | 30 | mA |
| Latch Current $(V_D = 12 \text{ V}, I_G = 15 \text{ mA})$ | | ΙL | 6.0 | 20 | 40 | mA |
| Gate Trigger Voltage (Continuous dc) $(V_D = 12 \text{ V}; 100 \Omega)$ | T _J = 25°C | V _{GT} | 0.5 | 0.65 | 1.0 | V |
| Gate Non–Trigger Voltage $(V_D = 12 \text{ V}; R_L = 100 \Omega)$ | T _J = 125°C | V _{GD} | 0.2 | - | - | V |
| DYNAMIC CHARACTERISTICS | | | | • | | • |
| Critical Rate of Rise of Off–State Voltage (V _D = Rated V _{DRM} , Exponential Waveform, Gate Open, T _J = 125°C) | | dv/dt | 100 | 250 | - | V/μs |
| Critical Rate of Rise of On–State Current IPK = 50 A, Pw = 40 μsec, diG/dt = 1 A/μsec, lgt = 50 mA | | di/dt | - | - | 50 | A/μs |

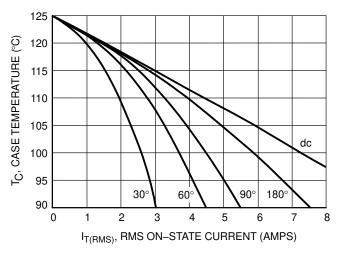
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Indicates Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2%.

Voltage Current Characteristic of SCR

| Symbol | Parameter |
|------------------|---|
| V _{DRM} | Peak Repetitive Off State Forward Voltage |
| I _{DRM} | Peak Forward Blocking Current |
| V _{RRM} | Peak Repetitive Off State Reverse Voltage |
| I _{RRM} | Peak Reverse Blocking Current |
| V_{TM} | Peak On State Voltage |
| I _H | Holding Current |

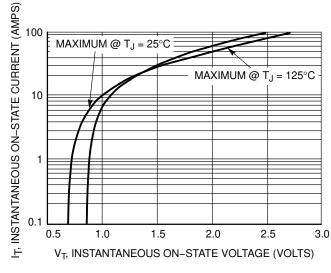




P(AV), AVERAGE POWER DISSIPATION (WATTS) 20 18 16 180° 90° 14 60° 12 30° 10 8 6 4 2 3 8 $I_{T(AV)}$, AVERAGE ON-STATE CURRENT (AMPS)

Figure 1. Typical RMS Current Derating

Figure 2. On-State Power Dissipation



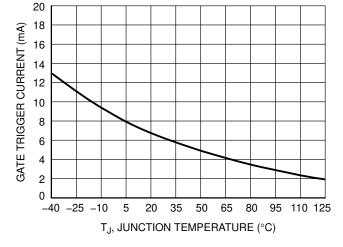


Figure 3. Typical On-State Characteristics

Figure 4. Typical Gate Trigger Current versus Junction Temperature

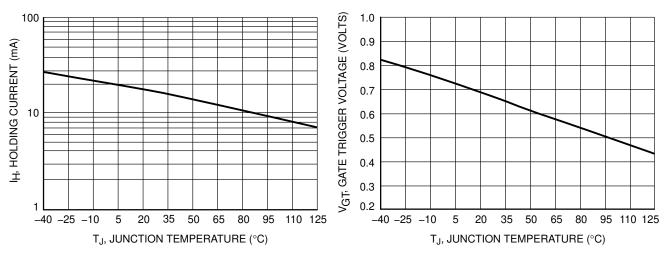


Figure 5. Typical Holding Current versus Junction Temperature

Figure 6. Typical Gate Trigger Voltage versus Junction Temperature

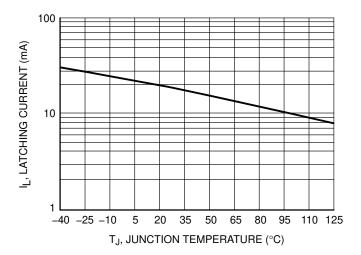
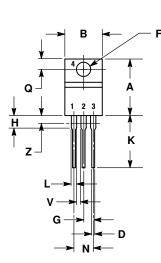
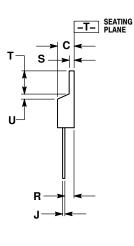


Figure 7. Typical Latching Current versus Junction Temperature

PACKAGE DIMENSIONS

TO-220 CASE 221A-09 **ISSUE AH**





- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
- DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

| | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 0.570 | 0.620 | 14.48 | 15.75 |
| В | 0.380 | 0.415 | 9.66 | 10.53 |
| С | 0.160 | 0.190 | 4.07 | 4.83 |
| D | 0.025 | 0.038 | 0.64 | 0.96 |
| F | 0.142 | 0.161 | 3.61 | 4.09 |
| G | 0.095 | 0.105 | 2.42 | 2.66 |
| Н | 0.110 | 0.161 | 2.80 | 4.10 |
| J | 0.014 | 0.024 | 0.36 | 0.61 |
| K | 0.500 | 0.562 | 12.70 | 14.27 |
| L | 0.045 | 0.060 | 1.15 | 1.52 |
| N | 0.190 | 0.210 | 4.83 | 5.33 |
| Q | 0.100 | 0.120 | 2.54 | 3.04 |
| R | 0.080 | 0.110 | 2.04 | 2.79 |
| S | 0.045 | 0.055 | 1.15 | 1.39 |
| T | 0.235 | 0.255 | 5.97 | 6.47 |
| U | 0.000 | 0.050 | 0.00 | 1.27 |
| ٧ | 0.045 | | 1.15 | |
| Z | | 0.080 | | 2.04 |

STYLE 3:

PIN 1. CATHODE

- 2. ANODE
- GATE
- ANODE

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